

DATA SHEET

74LVC00A Quad 2-input NAND gate

Product specification
Supersedes data of 2003 May 07

2003 Sep 04

Quad 2-input NAND gate

74LVC00A

FEATURES

- 5 V tolerant inputs for interfacing with 5 V logic
- Wide supply voltage range from 1.2 to 3.6 V
- CMOS low power consumption
- Direct interface with TTL levels
- Inputs accept voltages up to 5.5 V
- Complies with JEDEC standard no. 8-1A
- ESD protection:
HBM EIA/JESD22-A114-A exceeds 2000 V
MM EIA/JESD22-A115-A exceeds 200 V.
- Specified from -40 to $+85$ °C and -40 to $+125$ °C.

DESCRIPTION

The 74LVC00A is a high-performance, low-power, low-voltage, Si-gate CMOS device, superior to most advanced CMOS compatible TTL families.

Inputs can be driven from either 3.3 or 5 V devices. This feature allows the use of these devices as translators in a mixed 3.3 and 5 V environment.

Schmitt-trigger action at all inputs makes the circuit tolerant for slower input rise and fall times.

The 74LVC00A provides the 2-input NAND function.

QUICK REFERENCE DATA

GND = 0 V; $T_{amb} = 25$ °C; $t_r = t_f \leq 2.5$ ns.

SYMBOL	PARAMETER	CONDITIONS	TYPICAL	UNIT
t_{PHL}/t_{PLH}	propagation delay nA, nB to nY	$C_L = 50$ pF; $V_{CC} = 3.3$ V	2.1	ns
C_i	input capacitance		4.0	pF
C_{PD}	power dissipation capacitance per gate	$V_{CC} = 3.3$ V; notes 1 and 2	15	pF

Notes

1. C_{PD} is used to determine the dynamic power dissipation (P_D in μ W).

$$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o) \text{ where:}$$

f_i = input frequency in MHz;

f_o = output frequency in MHz;

C_L = output load capacitance in pF;

V_{CC} = supply voltage in Volts;

N = total load switching outputs;

$\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.

2. The condition is $V_i = \text{GND}$ to V_{CC} .

FUNCTION TABLE

See note 1.

INPUT		OUTPUT
nA	nB	nY
L	L	H
L	H	H
H	L	H
H	H	L

Note

1. H = HIGH voltage level;
L = LOW voltage level.

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ORDERING INFORMATION

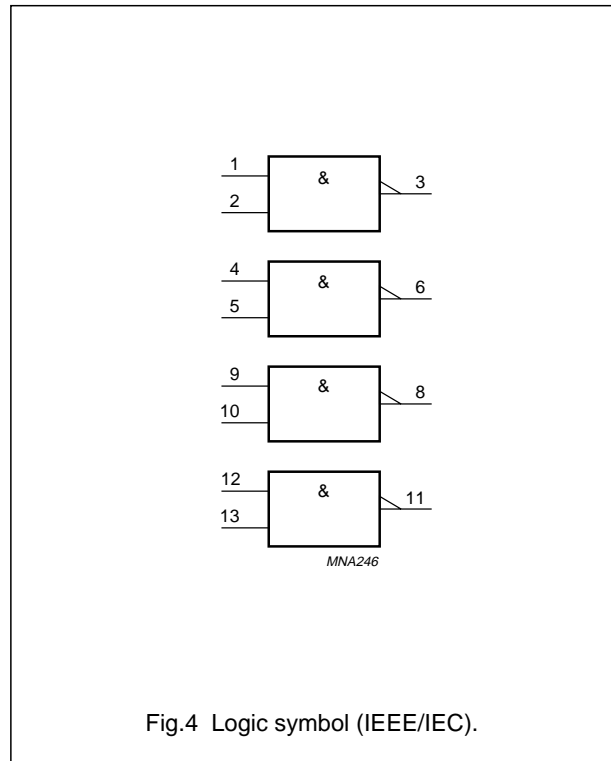
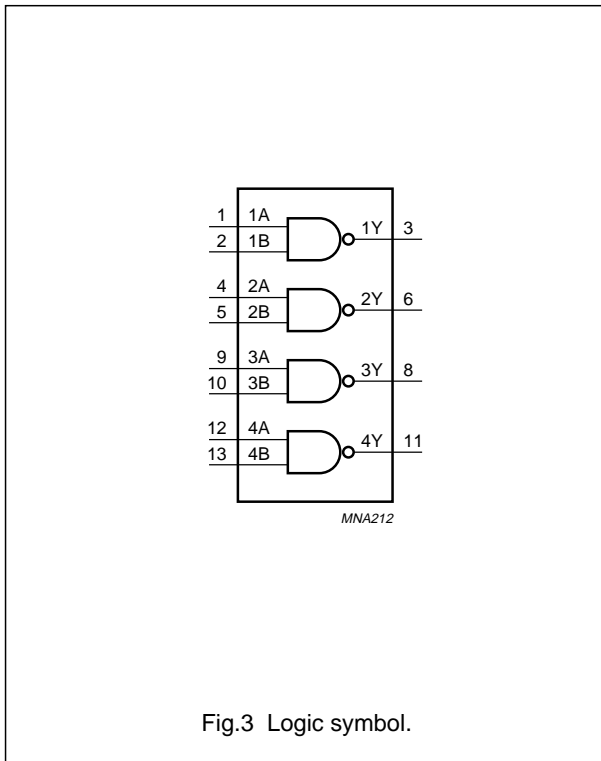
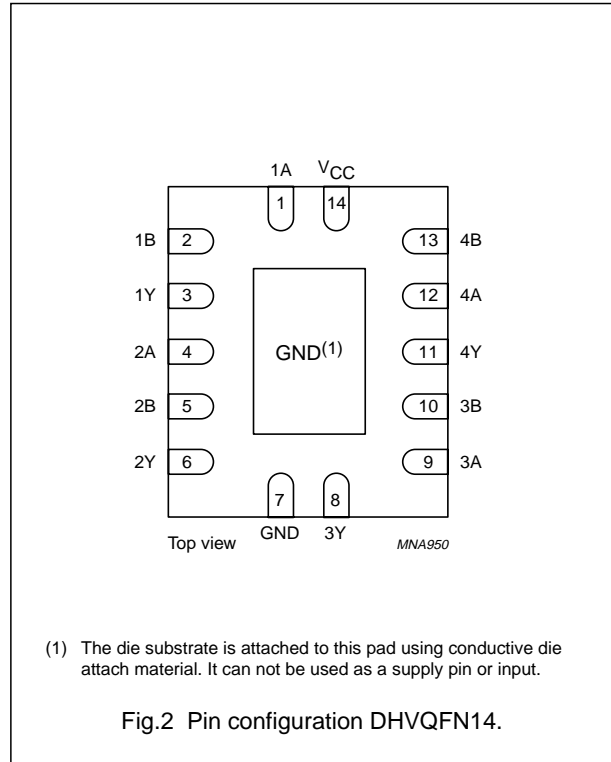
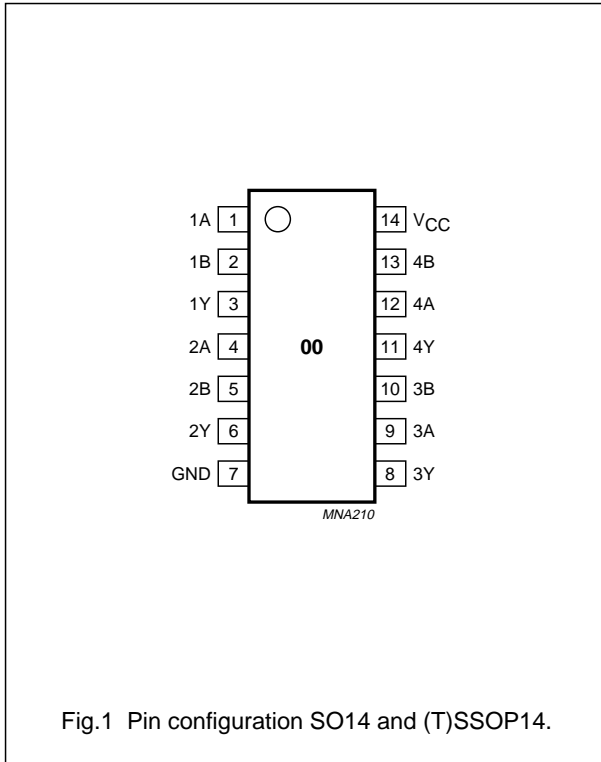
TYPE NUMBER	PACKAGE				
	TEMPERATURE RANGE	PINS	PACKAGE	MATERIAL	CODE
74LVC00AD	-40 to +125 °C	14	SO14	plastic	SOT108-1
74LVC00ADB	-40 to +125 °C	14	SSOP14	plastic	SOT337-1
74LVC00APW	-40 to +125 °C	14	TSSOP14	plastic	SOT402-1
74LVC00ABQ	-40 to +125 °C	14	DHVQFN14	plastic	SOT762-1

PINNING

PIN	SYMBOL	DESCRIPTION
1	1A	data input
2	1B	data input
3	1Y	data output
4	2A	data input
5	2B	data input
6	2Y	data output
7	GND	ground (0 V)
8	3Y	data output
9	3A	data input
10	3B	data input
11	4Y	data output
12	4A	data input
13	4B	data input
14	V _{CC}	supply voltage

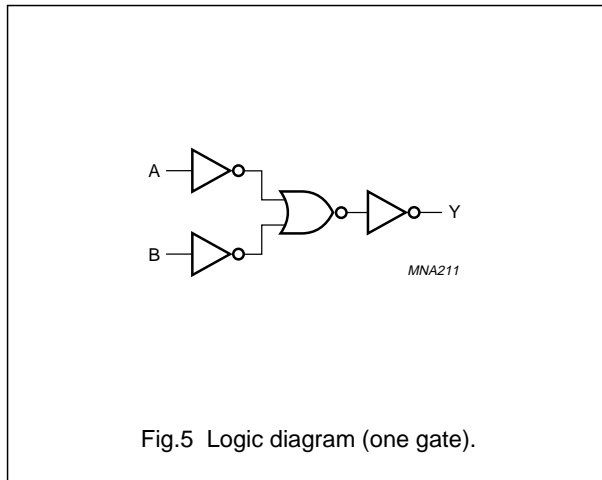
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RECOMMENDED OPERATING CONDITIONS

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CC}	supply voltage	for maximum speed performance	2.7	3.6	V
		for low-voltage applications	1.2	3.6	V
V_I	input voltage		0	5.5	V
V_O	output voltage		0	V_{CC}	V
T_{amb}	operating ambient temperature		-40	+125	°C
t_r, t_f	input rise and fall times	$V_{CC} = 1.2$ to 2.7 V	0	20	ns/V
		$V_{CC} = 2.7$ to 3.6 V	0	10	ns/V

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134); voltages are referenced to GND (ground = 0 V).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CC}	supply voltage		-0.5	+6.5	V
I_{IK}	input diode current	$V_I < 0$	-	-50	mA
V_I	input voltage	note 1	-0.5	+6.5	V
I_{OK}	output diode current	$V_O > V_{CC}$ or $V_O < 0$	-	± 50	mA
V_O	output voltage	note 1	-0.5	$V_{CC} + 0.5$	V
I_O	output source or sink current	$V_O = 0$ to V_{CC}	-	± 50	mA
I_{CC}, I_{GND}	V_{CC} or GND current		-	± 100	mA
T_{stg}	storage temperature		-65	+150	°C
P_{tot}	power dissipation	$T_{amb} = -40$ to $+125$ °C; note 2	-	500	mW

Notes

- The input and output voltage ratings may be exceeded if the input and output current ratings are observed.
- For SO14 packages: above 70 °C derate linearly with 8 mW/K.
For SSOP14 and TSSOP14 packages: above 60 °C derate linearly with 5.5 mW/K.
For DHVQFN14 packages: above 60 °C derate linearly with 4.5 mW/K.

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DC CHARACTERISTICS

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

SYMBOL	PARAMETER	TEST CONDITIONS		MIN.	TYP. ⁽¹⁾	MAX.	UNIT
		OTHER	V _{CC} (V)				
T_{amb} = -40 to +85 °C							
V _{IH}	HIGH-level input voltage		1.2	V _{CC}	-	-	V
			2.7 to 3.6	2.0	-	-	V
V _{IL}	LOW-level input voltage		1.2	-	-	GND	V
			2.7 to 3.6	-	-	0.8	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}	2.7 to 3.6	V _{CC} - 0.2	-	-	V
		I _O = -100 μA	2.7	V _{CC} - 0.5	-	-	V
		I _O = -12 mA	3.0	V _{CC} - 0.6	-	-	V
		I _O = -24 mA	3.0	V _{CC} - 0.8	-	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}	2.7 to 3.6	-	-	0.2	V
		I _O = 100 μA	2.7	-	-	0.4	V
		I _O = 24 mA	3.0	-	-	0.55	V
I _{LI}	input leakage current	V _I = 5.5 V or GND	3.6	-	±0.1	±5	μA
I _{CC}	quiescent supply current	V _I = V _{CC} or GND; I _O = 0	3.6	-	0.1	10	μA
ΔI _{CC}	additional quiescent supply current per input pin	V _I = V _{CC} - 0.6 V; I _O = 0	2.7 to 3.6	-	5	500	μA

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SYMBOL	PARAMETER	TEST CONDITIONS		MIN.	TYP. ⁽¹⁾	MAX.	UNIT
		OTHER	V _{CC} (V)				
T_{amb} = -40 to +125 °C							
V _{IH}	HIGH-level input voltage		1.2	V _{CC}	-	-	V
			2.7 to 3.6	2.0	-	-	V
V _{IL}	LOW-level input voltage		1.2	-	-	GND	V
			2.7 to 3.6	-	-	0.8	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}	2.7 to 3.6	V _{CC} - 0.3	-	-	V
		I _O = -100 μA	2.7	V _{CC} - 0.65	-	-	V
		I _O = -12 mA	3.0	V _{CC} - 0.75	-	-	V
		I _O = -24 mA	3.0	V _{CC} - 1	-	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}	2.7 to 3.6	-	-	0.3	V
		I _O = 100 μA	2.7	-	-	0.6	V
		I _O = 24 mA	3.0	-	-	0.8	V
I _{LI}	input leakage current	V _I = 5.5 V or GND	3.6	-	-	±20	μA
I _{CC}	quiescent supply current	V _I = V _{CC} or GND; I _O = 0	3.6	-	-	40	μA
ΔI _{CC}	additional quiescent supply current per input pin	V _I = V _{CC} - 0.6 V; I _O = 0	2.7 to 3.6	-	-	5000	μA

Note

1. All typical values are measured at V_{CC} = 3.3 V and T_{amb} = 25 °C.

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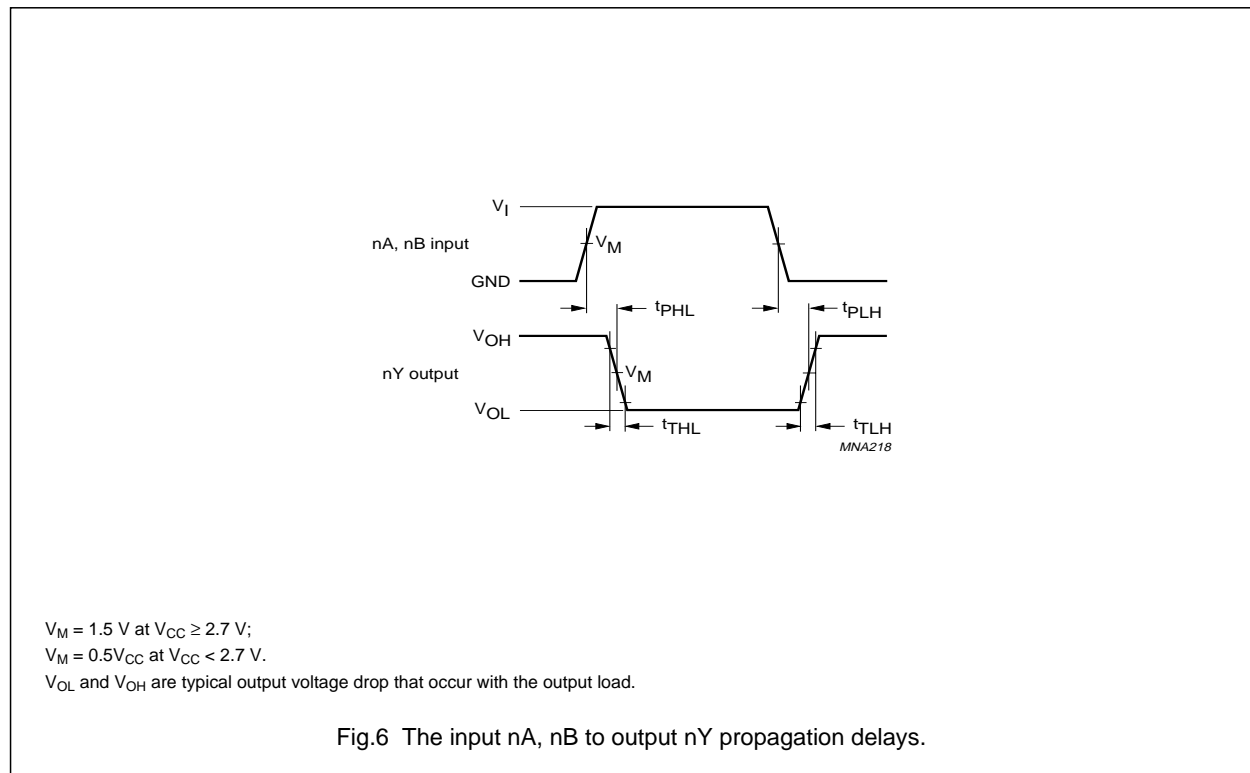
74LVC00A

AC CHARACTERISTICSGND = 0 V; $t_r = t_f \leq 2.5$ ns.

SYMBOL	PARAMETER	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
		WAVEFORMS	V_{CC} (V)				
$T_{amb} = -40$ to $+85$ °C							
t_{PHL}/t_{PLH}	propagation delay nA, nB to nY	see Figs 6 and 7	$V_{CC} = 1.2$	–	12	–	ns
			$V_{CC} = 2.7$	1.0	2.4	5.1	ns
			$V_{CC} = 3.0$ to 3.6	1.0	2.1 ⁽¹⁾	4.3	ns
$t_{sk(0)}$	skew	note 2	$V_{CC} = 3.0$ to 3.6	–	–	1.0	ns
$T_{amb} = -40$ to $+125$ °C							
t_{PHL}/t_{PLH}	propagation delay nA, nB to nY	see Figs 6 and 7	$V_{CC} = 1.2$	–	–	–	ns
			$V_{CC} = 2.7$	1.0	–	6.5	ns
			$V_{CC} = 3.0$ to 3.6	1.0	–	5.5	ns
$t_{sk(0)}$	skew	note 2	$V_{CC} = 3.0$ to 3.6	–	–	1.5	ns

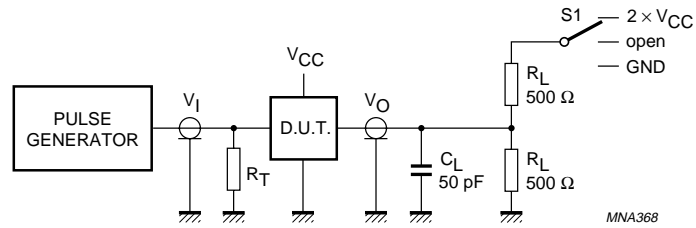
Notes

1. Typical value is measured at $V_{CC} = 3.3$ V.
2. Skew between any two outputs of the same package switching in the same direction. This parameter is guaranteed by design.

AC WAVEFORMS

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V_{CC}	V_I	t_{PLH}/t_{PHL}
1.2 V	V_{CC}	open
2.7 V	2.7 V	open
3.0 to 3.6 V	2.7 V	open

Definitions for test circuit:

R_L = Load resistor.

C_L = Load capacitance including jig and probe capacitance.

R_T = Termination resistance should be equal to the output impedance Z_o of the pulse generator.

Fig.7 Load circuitry for switching times.

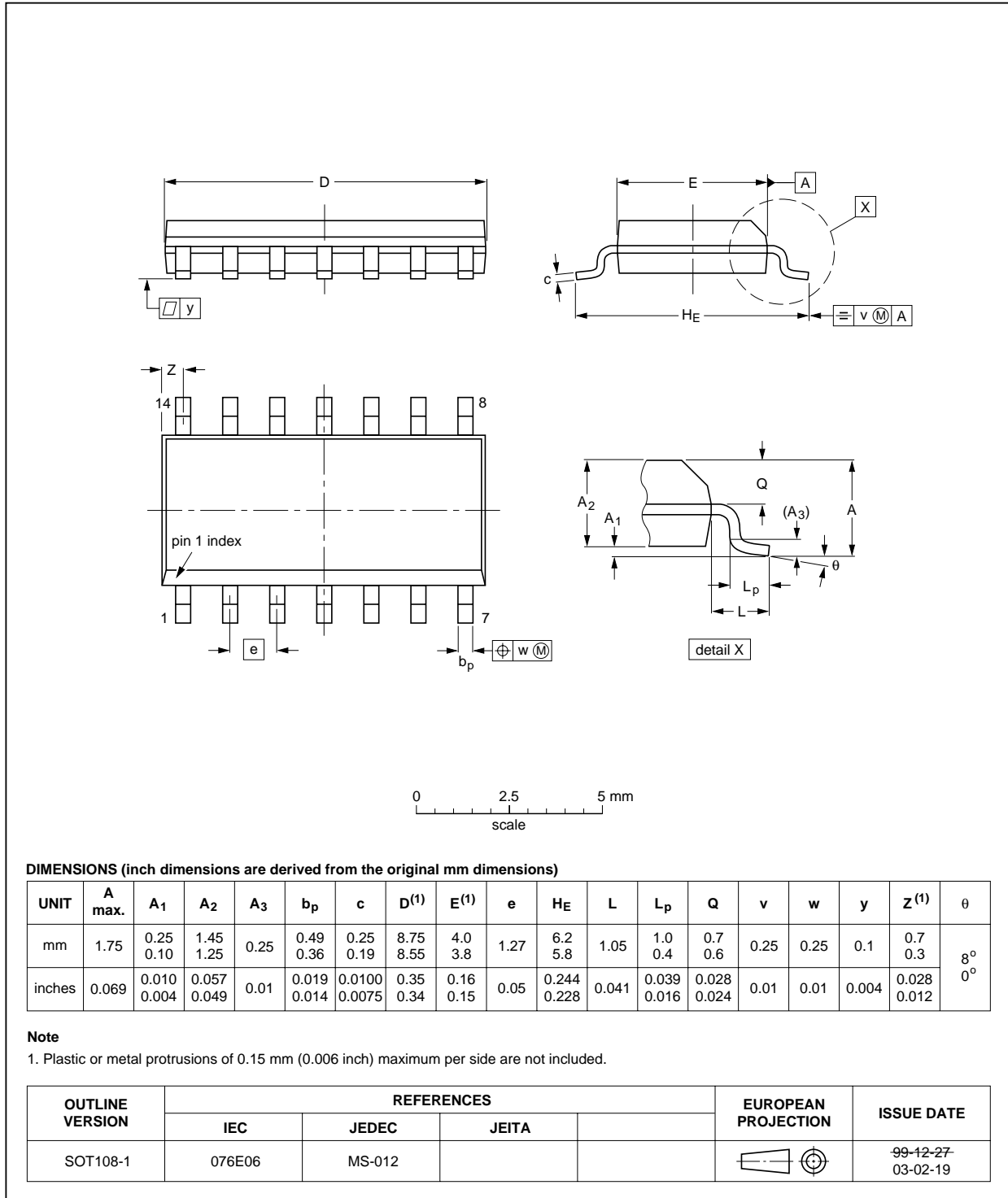
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PACKAGE OUTLINES

SO14: plastic small outline package; 14 leads; body width 3.9 mm

SOT108-1

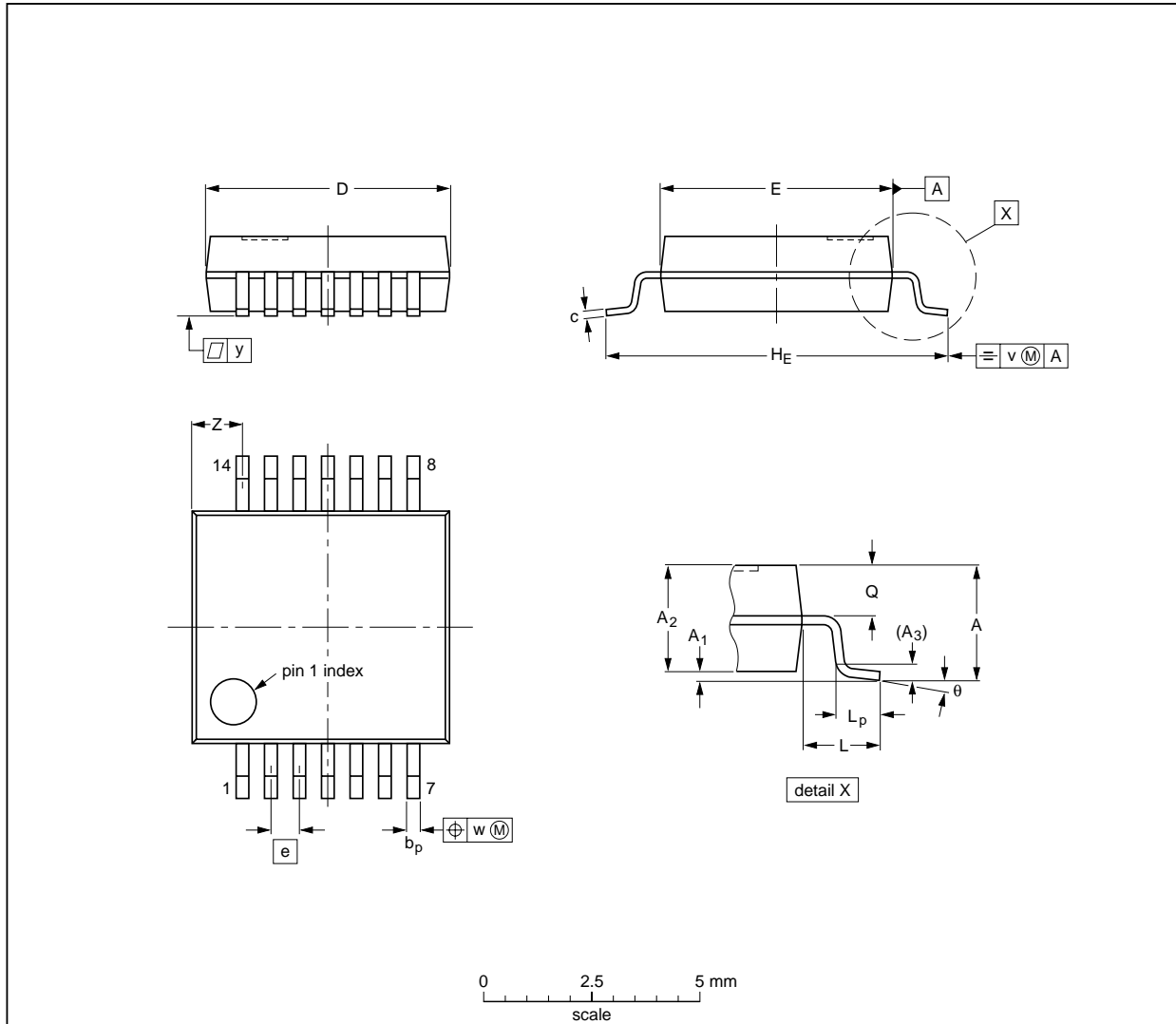


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SSOP14: plastic shrink small outline package; 14 leads; body width 5.3 mm

SOT337-1



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A ₁	A ₂	A ₃	b _p	c	D ⁽¹⁾	E ⁽¹⁾	e	H _E	L	L _p	Q	v	w	y	Z ⁽¹⁾	θ
mm	2	0.21 0.05	1.80 1.65	0.25	0.38 0.25	0.20 0.09	6.4 6.0	5.4 5.2	0.65	7.9 7.6	1.25	1.03 0.63	0.9 0.7	0.2	0.13	0.1	1.4 0.9	8° 0°

Note

1. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

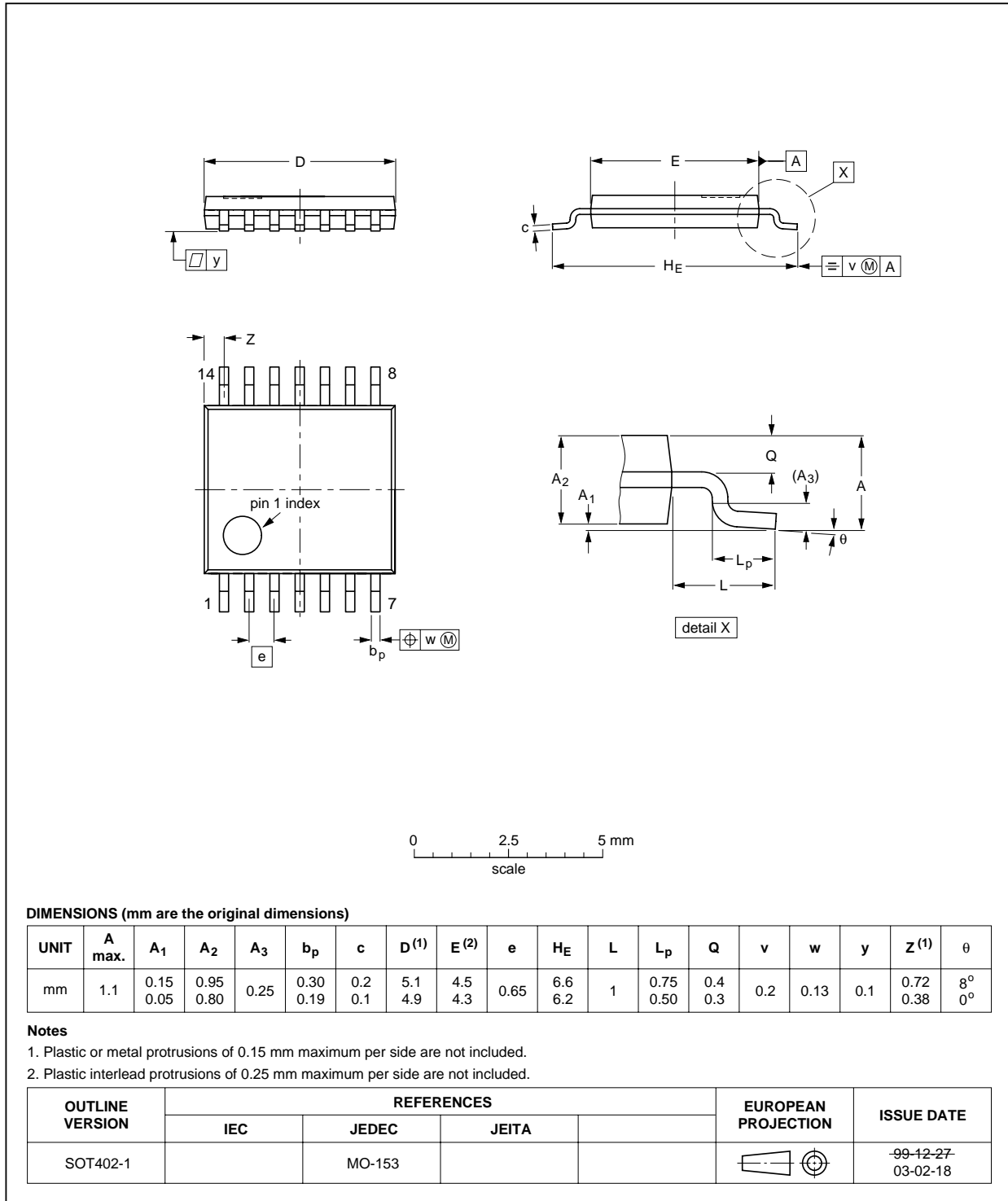
OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT337-1		MO-150				99-12-27 03-02-19

Quad 2-input NAND gate

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TSSOP14: plastic thin shrink small outline package; 14 leads; body width 4.4 mm

SOT402-1



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A ₁	A ₂	A ₃	b _p	c	D ⁽¹⁾	E ⁽²⁾	e	H _E	L	L _p	Q	v	w	y	z ⁽¹⁾	θ
mm	1.1	0.15 0.05	0.95 0.80	0.25	0.30 0.19	0.2 0.1	5.1 4.9	4.5 4.3	0.65	6.6 6.2	1	0.75 0.50	0.4 0.3	0.2	0.13	0.1	0.72 0.38	8° 0°

Notes

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

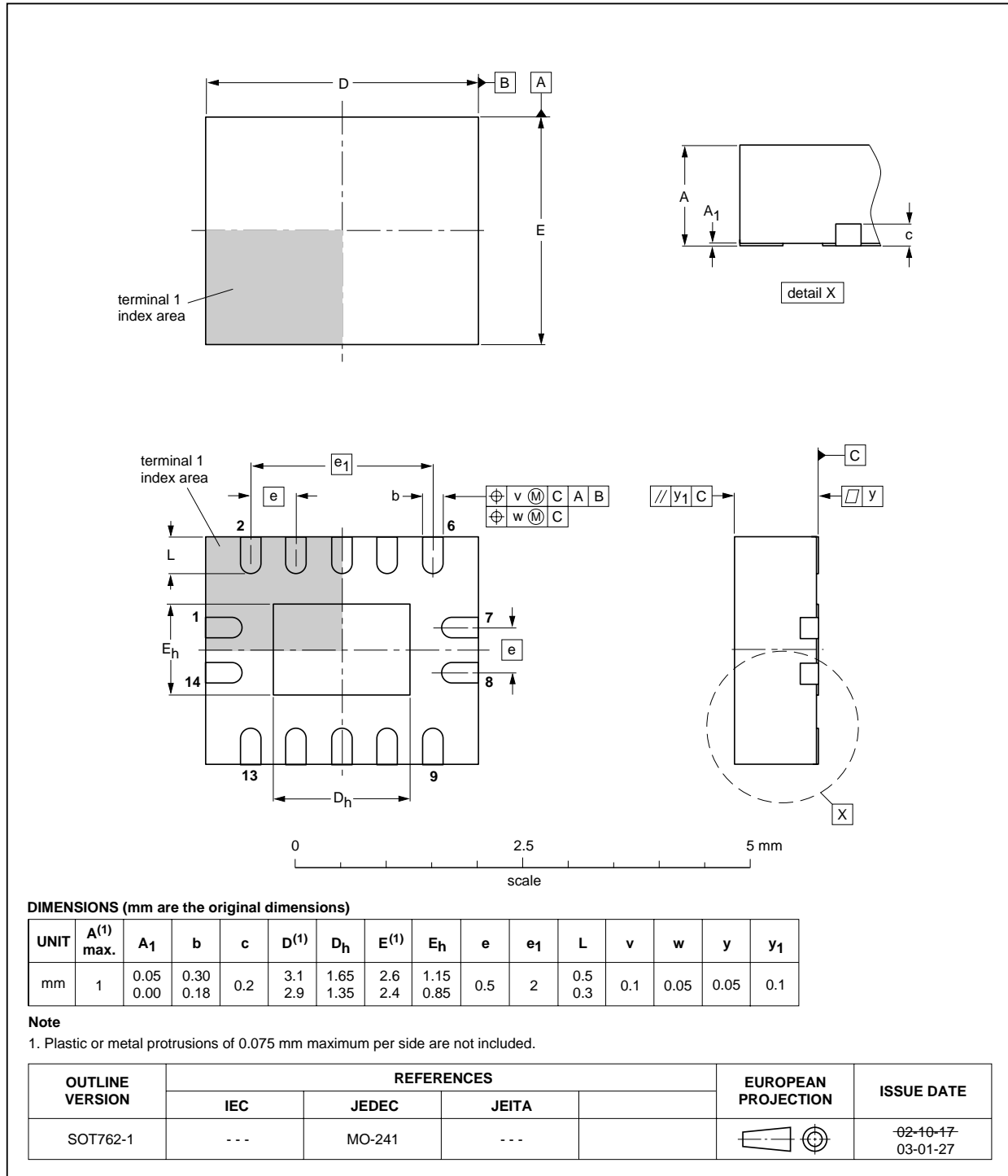
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	IEC	JEDEC	JEITA			
SOT402-1		MO-153				99-12-27 03-02-18

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DHVQFN14: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 14 terminals; body 2.5 x 3 x 0.85 mm

SOT762-1



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DATA SHEET STATUS

LEVEL	DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾⁽³⁾	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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